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S/N 09/961,036

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Madhav Datta et al.

Examiner: Erik J. Kielin

Serial No.: 09/961,036

Group Art Unit: 2811

Filed: September 21, 2001

Docket: 884.523US1

Title: DUAL-STACK, BALL-LIMITING METALLURGY
AND METHOD OF MAKING SAME

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ELECTION OF CLAIMS AND PRELIMINARY AMENDMENT UNDER 37 CFR § 1.115

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Restriction Requirement mailed on May 13, 2002.

In response to the Restriction Requirement, the Applicant elects without traverse, Group II, claims 17-30. Applicant cancels remaining claims 1-16 without prejudice or disclaimer and reserves the right to reintroduce these claims in one or more divisional applications at a later date.

Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please add new claims 31-45.

31. (New) The process according to claim 17, wherein forming a refractory metal first layer over the metallization includes sputtering Ti over the metallization to a thickness in a range from about 500 Å to about 2,000 Å, and wherein forming a refractory metal second layer over the refractory metal first layer includes sputtering NiV over the refractory metal first layer to a thickness in a range from about 1,000 Å to about 4,000 Å.

32. (New) The process according to claim 17, wherein forming a refractory metal first layer over the metallization includes sputtering Ti over the metallization to a thickness in a range from about 500 Å to about 2,000 Å, wherein forming a refractory metal second layer over the refractory metal first layer includes sputtering NiV over the refractory metal first layer to a